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THE UNITED STATES PATENT AND TRADEMARK OFFICE
BOARD OF PATENT APPEALS AND INTERFERENCES

In Re Application of : Vladislav Vashchenko)

Serial No.: 09/944,426)

Examiner: Ori Nadav

Filed: 8/30/2001)

Art Unit: 2811

For: HIGH HOLDING VOLTAGE
LVTSCR-LIKE STRUCTURE)

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APPEAL BRIEF
IN SUPPORT OF APPELLANTS' APPEAL
TO THE BOARD OF PATENT APPEALS AND INTERFERENCES

Hon. Commissioner of
Patents and Trademarks
Washington, DC 20231

Dear Sir:

The Appellants hereby submit this Brief in triplicate in support of their appeal from a final rejection by the Examiner, mailed April 17, 2003 and follow-up Advisory Action mailed August 8, 2003, in the above case. The Appellants respectfully request consideration of this appeal by the Board of Patent Appeals and Interferences for allowance of the above patent application.

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Serial No. 09/944,426

APPEAL BRIEF

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I. REAL PARTY IN INTEREST

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II. RELATED APPEALS AND INTERFERENCES

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There are no related appeals or interferences

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III. STATUS OF THE CLAIMS

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Claims 1-6 are currently pending. Claim 1 is withdrawn from consideration and is

not being appealed.

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IV. STATUS OF AMENDMENTS

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No after final amendment was made.

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V. SUMMARY OF INVENTION

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The invention relates to a LVTSCR-like structure for electrostatic discharge (ESD) protection, which has a higher holding voltage than a prior art LVTSCR, by including additional p and n regions in a p-well, to define at least one forward biased p-n junction in the p-well.

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VI. ISSUES

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The issue is whether the prior art cited, namely Ham, discloses a structure having a p-n junction in the p-well that is forward biased during normal operation.

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VII. GROUPING OF CLAIMS

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Claims 2-6 were rejected based on the common argument that Ham anticipates the invention defined in the claims.

VIII. ARGUMENT

Summary of arguments:

Claims 2-6 were rejected under 35 USC 102(b) in view of Ham.

The examiner argues that Ham teaches in figure 7 a method that includes providing a p-n junction diode 40,42 in the p-well that is forward biased during normal operation.

It is respectfully submitted that there is no forward biased p-n junction anywhere in Ham. In fact the only biased junctions are the following:

- a) The p-well/n-well junction, which is reverse biased (n-well connected to VDD and p-well connected to VSS).
- b) A reverse biased junction between p+ region 48 (tied to I/O pad) and n-well (tied to the higher voltage VDD). This is described in column 4, lines 59-67 and shown in Figure 8 as reverse biased diode 56.
- c) A reverse biased diode between the p-well (tied to VSS) and n+ region 44 (tied to the I/O pad). This is shown in Figure 8 as reverse biased diode 54).

(The regions 40, 42 are both tied to VSS and therefore the p-n junctions across these two regions is not biased. Similarly the regions 50, 52 are both tied to VDD and therefore the junction between them is also not biased.)

Thus, Ham has no forward biased junctions.

In contrast to Ham, the present application has two p-n junctions in the p-well, namely (p+ region 420/n+ region 422) and (p+ region 424/n+ region 426) (see page 5, lines 36-38). The electric field across the structure between drain 406, 408 and source, biases the two diodes in a forward direction to provide the additional current path when they break down at approximately 1V (see page 6, lines 12-14).

The examiner argues that Vdd can be positive or negative and refers to column 4, lines 59-62. There is no such support in the cited section of Ham.

The examiner also argues that the limitation of a forward biased p-n junction is not recited in the claims. However the amendment filed February 10, 2003 clearly includes this limitation. In the case of claim 3 it is stated that the current path is from anode to cathode, which is also not disclosed in Ham.

107 Since Claims 2-6 are distinguishable over the prior art, allowance of the claims 2-6 is
108 respectfully requested.

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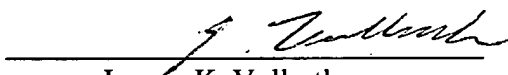
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Charge Our Deposit Account

If there are any further charges not accounted for herein, please charge them to our
deposit account No. 140448

Respectfully submitted,
Vollrath & Associates

Date: 8/16/, 2003


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138 **IX. APPENDIX**

- 139 2. A method of increasing the holding voltage of a LVTSCR structure,
140 comprising forming at least one additional p-region and n-region
141 inside a p-well of the structure to define a p-n junction that is forward
142 biased during normal operation.
- 143 3. A method of increasing the holding voltage of a LVTSCR-like
144 structure having an anode and a cathode, comprising providing an
145 alternative current path from anode to cathode through a p-well of the
146 structure, other than purely the current path from anode to cathode
147 through the p-material of the p-well.
- 148 4. A method of claim 3, wherein the alternative current path defines a
149 lower resistance current path than the p-well.
- 150 5. A method of claim 4, wherein the lower resistance current path takes
151 the form of at least one p-n junction that is forward biased under
152 normal operating conditions, formed in the p-well.
- 153 6. A method of claim 4, wherein at least one diode is formed in the p-
154 well which provides a low resistance current path once the voltage
155 across the at least one diode is exceeded.